RT1P141X SERIES

(Transistor) Transistor With Resistor For Switching Application Silicon PNP Epitaxial Type

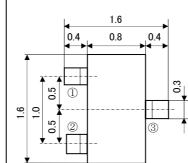
OUTLINE DRAWING

DESCRIPTION

RT1P141X is a one chip transistor with built-in bias resistor,NPN type is RT1N141X.

FEATURE

•Built-in bias resistor (R1=10k Ω ,R2=10k Ω).



0.1

6

JEITA : -

JEDEC : -

Terminal Connector

1):Base

2: Emitter

3: Collector

RT1P141M

2.1

1.25

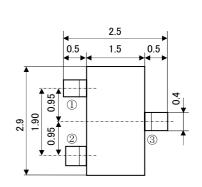
0.425

0.3

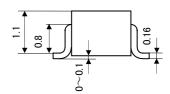
0.425

1

0.7 0.55 RT1P141U



RT1P141C



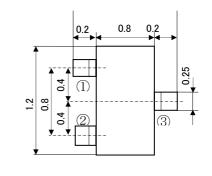
JEITA: SC-59 JEDEC: Similar to TO-236

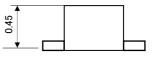
Terminal Connector

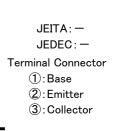


- 2: Emitter
- 3: Collector

RT1P141T



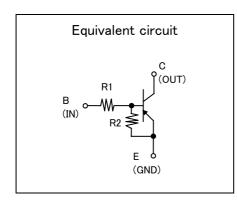


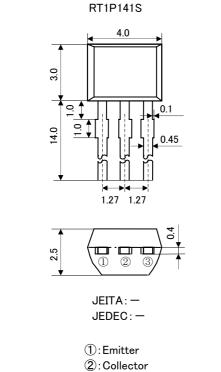


UNIT:mm

APPLICATION

Inverted circuit, switching circuit, interface circuit, driver circuit.





③:Base

0.9 0.7 $0 \sim 0.1$

0.65

0.65

2.0 1.3

> JEITA: SC-70 JEDEC: -Terminal Connector (1):Base (2): Emitter 3: Collector

> > www.DataSheet4U.com

ISAHAYA ELECTRONICS CORPORATION

RT1P141X SERIES

(Transistor)

Transistor With Resistor

For Switching Application

Silicon PNP Epitaxial Type

MAXIMUM RATING (Ta=25°C)

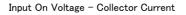
SYMBOL	PARAMETER	RATING					
		RT1P141T	RT1P141U	RT1P141M	RT1P141C	RT1P141S	UNIT
V _{CBO}	Collector to Base voltage	-50					
V _{EBO}	Emitter to Base voltage	-10					
V _{CEO}	Collector to Emitter voltage	-50					V
Ι _c	Collector current	-100					
I _{CM}	Peak Collector current	-200					mA
Pc	Collector	125(※)	125	15	50	450	mW
	dissipation(Ta=25°C)						11144
Tj	Junction temperature	+125		+150			°C
Tstg	Storage temperature	-55~+125		-55~+150			°C

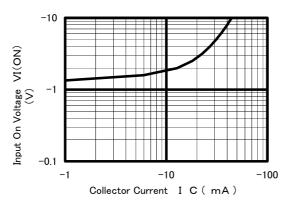
ELECTRICAL CHARACTERISTICS (Ta=25°C)

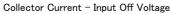
(%) package mounted on 9mm × 19mm × 1mm glass-epoxy substrate.

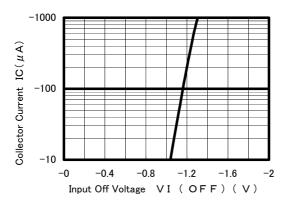
SYMBOL	PARAMETER	TEST CONDITION	LIMIT			UNIT
		TEST CONDITION	MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$	C to E break down voltage	$I_{c} = -100 \mu A, R_{BE} = \infty$	-50			V
I _{CBO}	Collector cut off current	V _{CB} =-50V, I _E =0			-0.1	μA
h _{FE}	DC forward current gain	V _{CE} =-5V, I _C =-10mA	50			—
$V_{CE(sat)}$	C to E saturation voltage	I _c =–10mA, I _B =–0.5mA		-0.1	-0.3	V
V _{I(ON)}	Input on voltage	V _{CE} =-0.2V, I _C =-5mA		-1.5	-3.0	V
$V_{I(OFF)}$	Input off voltage	V_{ce} =-5V, I _c =-100 μ A	-0.8	-1.1		V
R ₁	Input resistance		7.0	10	13	kΩ
R_2 / R_1	Resistance ratio		0.9	1.0	1.1	
f⊤	Gain band width product	V _{CE} =-6V, I _E =10mA		150		MHz

TYPICAL CHARACTERISTICS

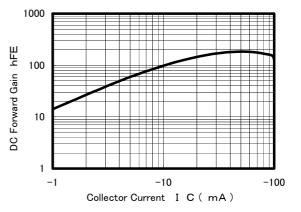








DC Forward Gain - Collector Current



ISAHAYA ELECTRONICS CORPORATION



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